

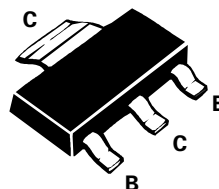
PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ISSUE 1 - JANUARY 1997

FZT1147A

FEATURES

- * $V_{CEO} = -12V$
- * 5 Amp Continuous Current
- * 20 Amp Pulse Current
- * Low Saturation Voltage
- * High Gain



SOT223

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-15	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-20	A
Continuous Collector Current	I_C	-5	A
Base Current	I_B	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$ †	P_{tot}	2.5	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

†The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 2 inches by 2 inches

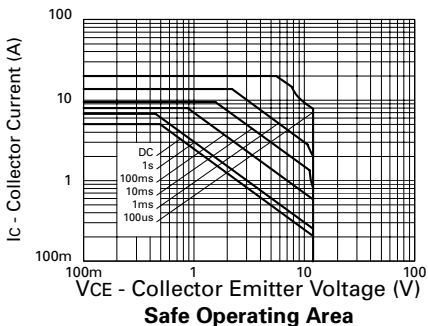
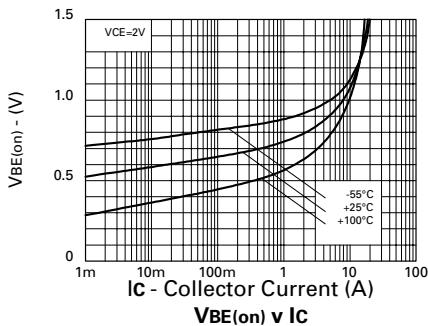
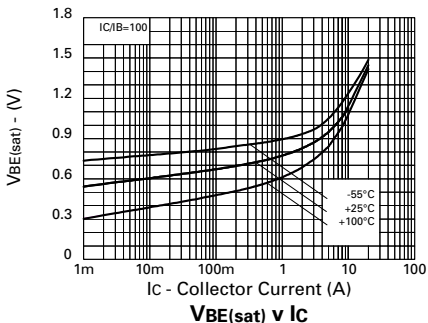
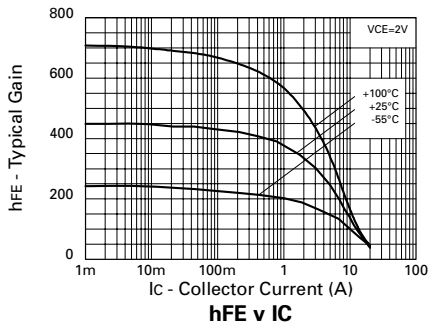
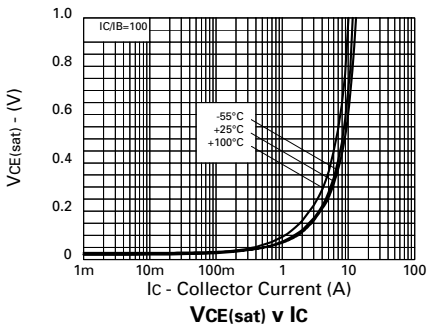
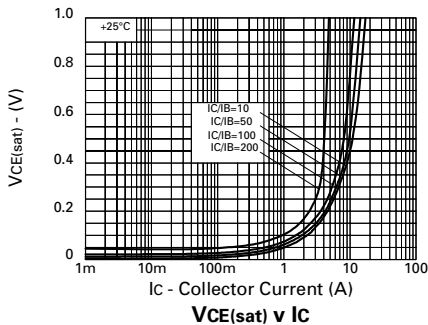
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	VALUE			UNIT	CONDITIONS.
		MIN.	TYP.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-15	-35		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CES}	-12	-25		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	V_{CEO}	-12	-25		V	$I_C = -10\text{mA}$ *
Collector-Emitter Breakdown Voltage	V_{CEV}	-12	-25		V	$I_C = -100\mu\text{A}$, $V_{EB} = +1\text{V}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-8.5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-0.3	-100	nA	$V_{CB} = -12\text{V}$
Emitter Cut-Off Current	I_{EBO}		-0.3	-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}		-0.3	-100	nA	$V_{CE} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-25	-50	mV	$I_C = -0.1\text{A}$, $I_B = -1.0\text{mA}$ *
			-70	-110	mV	$I_C = -0.5\text{A}$, $I_B = -2.5\text{mA}$ *
			-90	-130	mV	$I_C = -1\text{A}$, $I_B = -6\text{mA}$ *
			-115	-170	mV	$I_C = -2\text{A}$, $I_B = -20\text{mA}$ *
			-250	-400	mV	$I_C = -5\text{A}$, $I_B = -50\text{mA}$ *
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-950	-1050	mV	$I_C = -5\text{A}$, $I_B = -50\text{mA}$ *
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-905	-1000	mV	$I_C = -5\text{A}$, $V_{CE} = -2\text{V}$ *
Static Forward Current Transfer Ratio	h_{FE}	270	450	850		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$ *
		250	400			$I_C = -0.5\text{A}$, $V_{CE} = -2\text{V}$ *
		200	340			$I_C = -2\text{A}$, $V_{CE} = -2\text{V}$ *
		150	245			$I_C = -5\text{A}$, $V_{CE} = -2\text{V}$ *
		90	145			$I_C = -10\text{A}$, $V_{CE} = -2\text{V}$ *
			50			$I_C = -20\text{A}$, $V_{CE} = -2\text{V}$ *
Transition Frequency	f_T		115		MHz	$I_C = -50\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{cb}		80		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on}		150		ns	$I_C = -4\text{A}$, $I_B = -40\text{mA}$, $V_{CC} = -10\text{V}$
	t_{off}		220		ns	$I_C = -4\text{A}$, $I_B = \pm 40\text{mA}$, $V_{CC} = -10\text{V}$

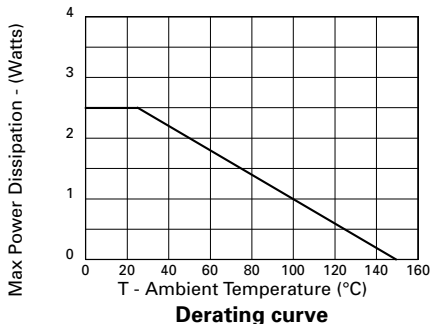
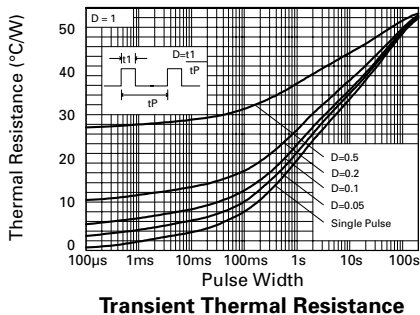
*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS



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THERMAL CHARACTERISTICS



SPICE PARAMETERS

* ZETEX FZT1147A Spice model Last revision 10/12/96

*

.MODEL FZT1147A PNP IS=1.272e-12 NF=0.989 ISE=2.5e-13 NE=1.65

+ BF=500 VAF=14.59 IKF=8 NR=1 ISC=8e-14 NC= 1.6

+ BR=90 VAR=3.1 IKR=1.2 RE=15e-3 RB=145e-3

+ RC=13e-3 CJE=560e-12

+ CJC=255e-12 VJC=0.6288

+ MJC=0.4048 TF=1.2e-9 TR=13e-9

*

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